In the Claims:

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- 1. (original) A method of fabricating a semiconductor device

 2 by employing ion implantation to provide a semiconductor

 3 substrate (1) at a surface thereof with a region having

 4 dopant introduced therein, comprising the steps of:

 5 providing said semiconductor substrate (1) at a surface

 6 thereof with a mask layer including a polyimide resin film

 7 (2); and implanting dopant ions (5).
- 2. (original) A method of fabricating a semiconductor device 1 2 by employing ion implantation to provide a semiconductor substrate (101) at a surface thereof with a region having 3 introduced therein, comprising the steps providing said semiconductor substrate (101) at a surface 5 thereof with a mask layer (103) including a SiO, film (107a, 107b) and a thin metal film (105); and implanting dopant 7 ions (5). 8

Claims 3 to 5 (canceled).

- 6. (original) The method of claim 1, wherein said semiconductor substrate (1) is heated to at least 300°C and dopant ions (5) are implanted.
- 7. (original) The method of claim 1, wherein said semiconductor substrate (1) is heated to at least 500°C and dopant ions (5) are implanted.

- 1 8. (original) The method of claim 1, wherein said polyimide resin film (2) is formed of photosensitive polyimide resin.
- 9. (original) The method of claim 1, wherein said polyimide
 resin film (2a) has a thickness of at least twice a depth
 of dopant introduced into said semiconductor substrate (1)
 at a region free of said polyimide resin film (2a).
- 1 10. (original) The method of claim 1, wherein a thin metal film
 2 is posed between said polyimide resin film (2a) and said
 3 semiconductor substrate (1).
- 1 11. (original) The method of claim 1, wherein a thin film
 2 formed of SiO₂ is posed between said polyimide resin film
 3 (2a) and said semiconductor substrate (1).
- 1 12. (original) The method of claim 2, wherein said
 2 semiconductor substrate (101) is heated to at least 300°C
 3 to 500°C and dopant ions are implanted.
- 1 13. (original) The method of claim 2, wherein said
 2 semiconductor substrate (101) is heated to at least 500°C
 to 800°C and dopant ions are implanted.
- 1 14. (original) The method of claim 2, wherein said mask layer
 2 (103) is formed of at least three layers.

- 1 15. (original) The method of claim 2, wherein said SiO_2 film (107a, 107b) and said thin metal film (105) each have an average thickness of 500 nm to 1.5 μ m.
- 1 16. (original) The method of claim 2, wherein said mask layer
 2 (103) includes a SiO₂ film as a film corresponding to a
 3 bottommost layer.
- 1 17. (original) The method of claim 2, wherein said mask layer
 2 (103) includes a thin metal film as a film corresponding to
 3 a bottommost layer.
- 1 18. (original) The method of claim 2, wherein said mask layer
 2 (103) includes a SiO₂ film as a film corresponding to a
 topmost layer.
- 1 19. (original) The method of claim 2, wherein said mask layer
 2 (103) includes a thin metal film as a film corresponding to
 3 a topmost layer.
- 1 20. (original) The method of claim 2, wherein said SiO₂ film
 2 (107a, 107b) is formed by SOG.

[REMARKS FOLLOW ON NEXT PAGE]